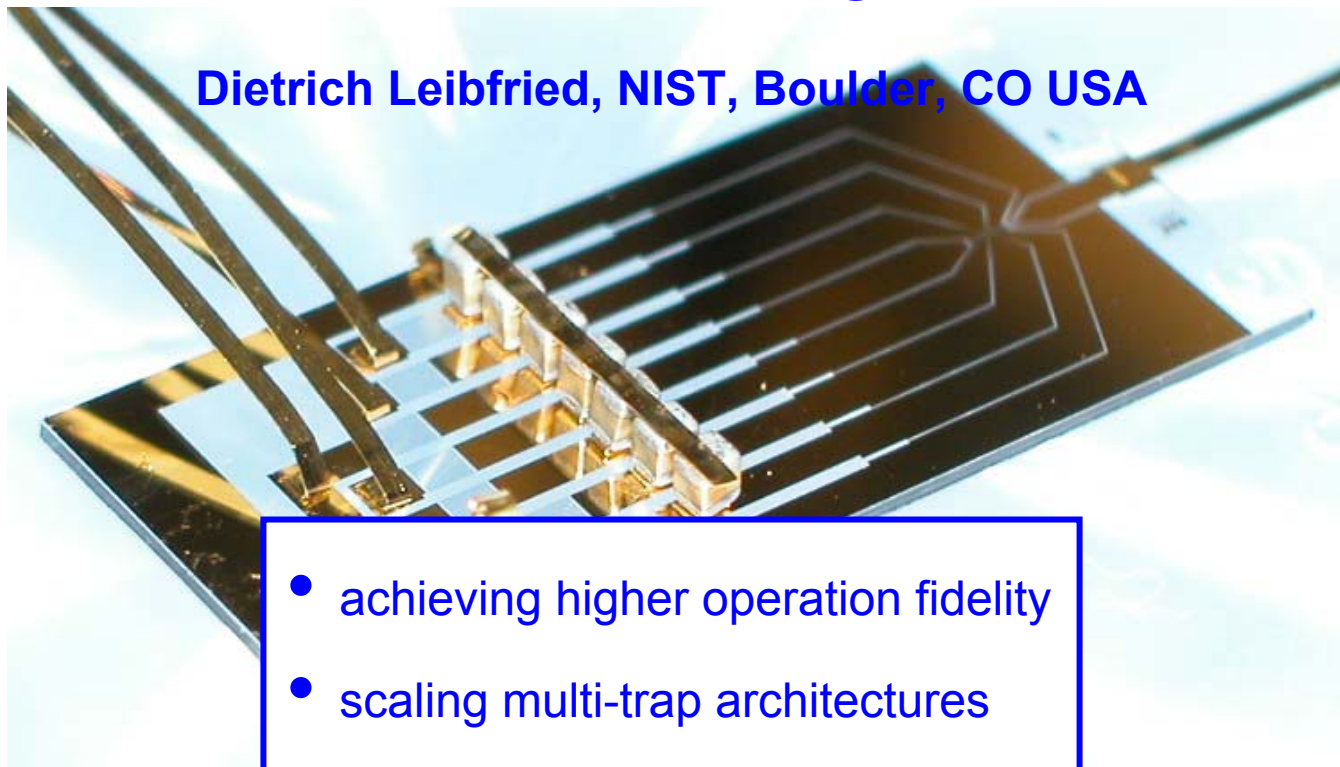


# Challenges for ion trap quantum computing



- achieving higher operation fidelity
- scaling multi-trap architectures
- large scale classical control
- fault tolerance



ARDA

NIST

# NIST ion storage group

(April 26 2005)



Brad Blakestad (grad student, CU)

Jim Beall (NIST, Cryoelectronics)

Joe Britton (grad student, CU)

**John Bollinger**

John Chiaverini (postdoc, Stanford)

Ryan Epstein (postdoc, UCSB)

**Wayne Itano**

John Jost (grad student, CU)

**Manny Knill (NIST, computer science)**

Chris Langer (grad student, CU)

**Dietrich Leibfried**

Roe Ozeri (postdoc, Haifa)

Rainer Reichle (postdoc, Freiburg)


Till Rosenband

Signe Seidelin (postdoc, Orsay)

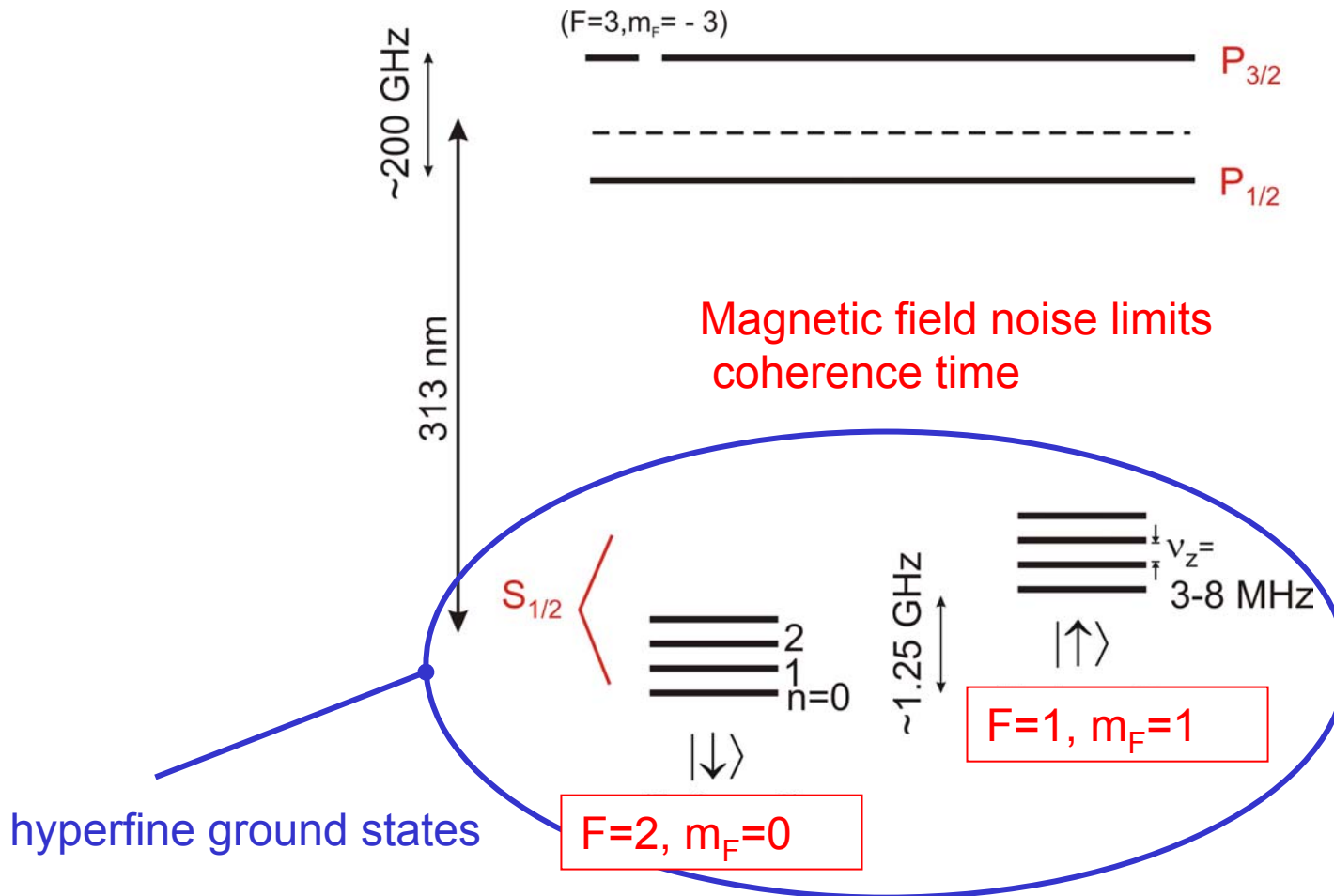
Janus Wesenberg (postdoc, Aarhus)

**David Wineland**

# DiVincenzo requirements

- I. A scalable physical system with well characterized qubits
- II. The ability to initialize the state of the qubits to a simple fiducial state  
optical pumping, ground-state cooling (99.9%) 
- III. Long relevant decoherence times, much longer than the gate time  
Hyperfine ground states
- IV. A universal set of quantum gates (single qubit rot., two qubit gate)
- V. A qubit-specific read out capability

# Example ion qubit: ${}^9\text{Be}^+$



# Low memory error qubits

## **optical qubits:**

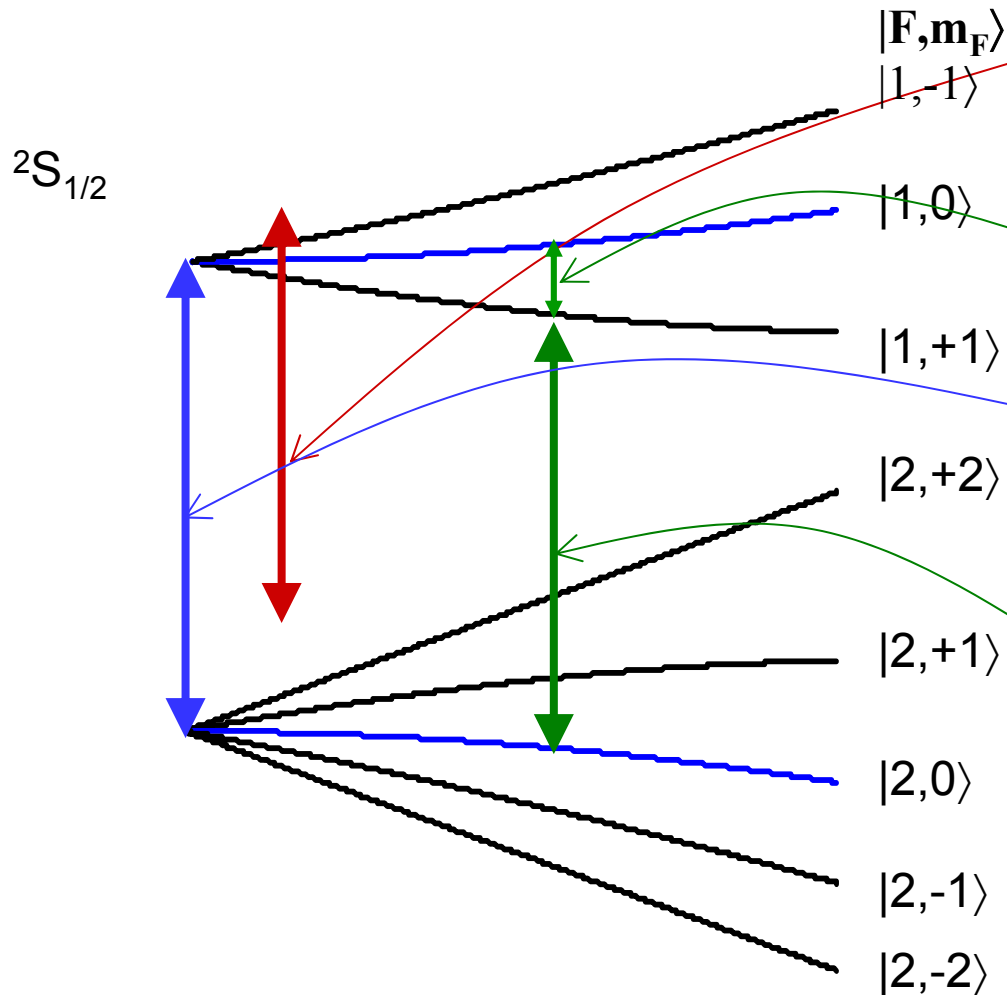
- state lifetimes  $<$  conceivable computation time  $\Rightarrow$  spontaneous emission errors, hard to correct
- coherence times limited by laser and environ.  $\Rightarrow$  memory phase errors

## **hyperfine qubits:**

- state lifetimes  $\gg$  conceivable computation time  $\Rightarrow$  no intrinsic bit flip errors
- coherence times depend on environment  $\Rightarrow$  memory phase errors dominate

# Low memory error qubits

magnetic field dependence:



$|2, 2\rangle \leftrightarrow |1, 1\rangle$   
 $\delta f / \delta B = -2.1 \text{ MHz/G}$   
for  $\delta B = 1 \text{ mG}$   
 $\tau_2(\delta\phi = 1 \text{ rad}) \cong 76 \mu\text{s}$

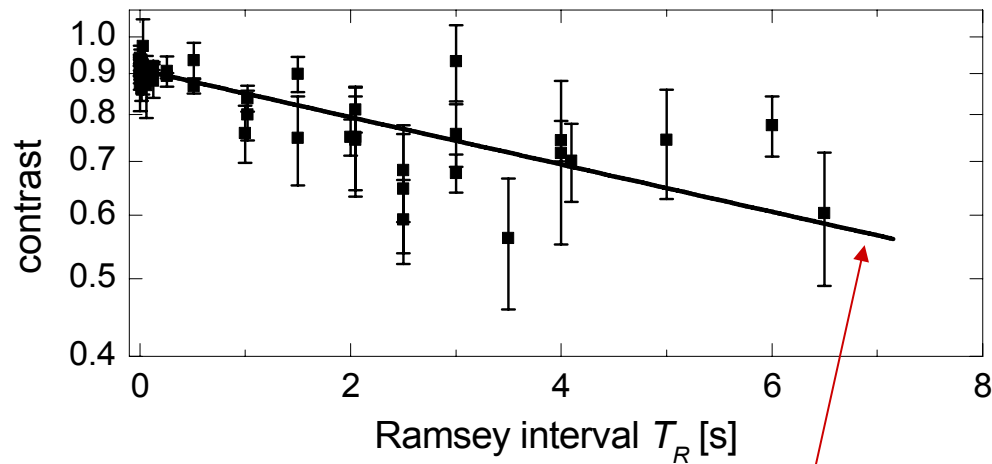
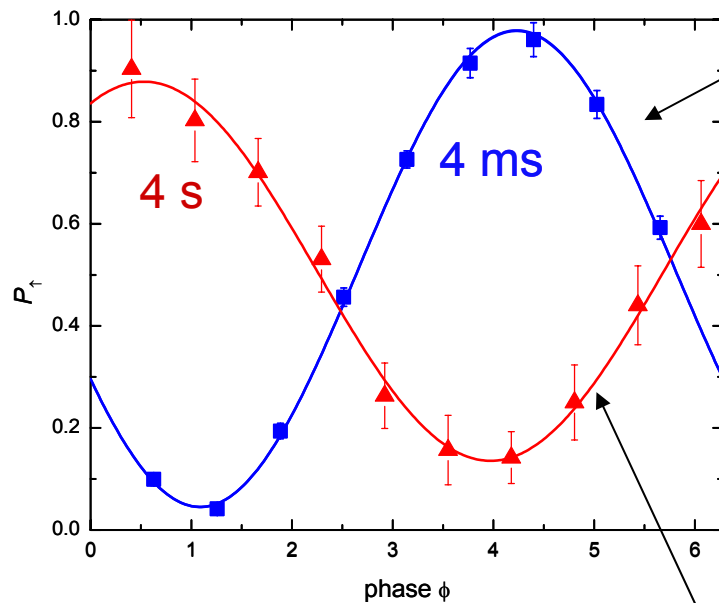
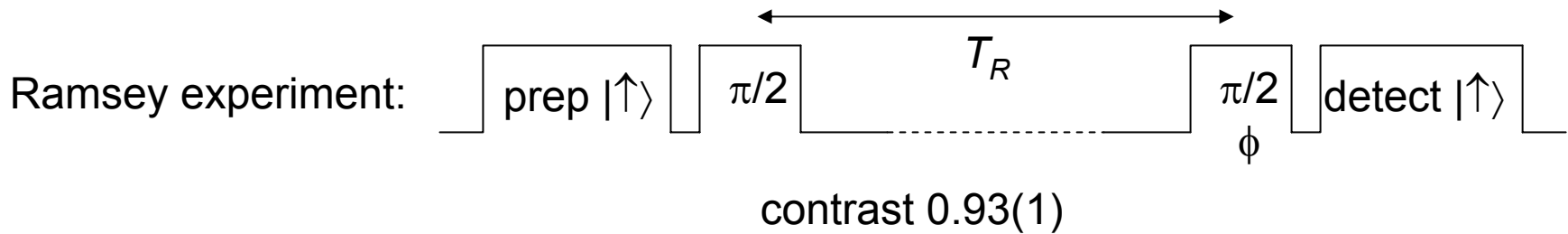
Substantial level splitting  
 $\Rightarrow$  off-resonant excitations  
 suppressed

$|2, 0\rangle \leftrightarrow |1, 0\rangle$   
 field-independent at  $B = 0$   
 $m_F$  levels are degenerate

$|2, 0\rangle \leftrightarrow |1, 1\rangle$   
 $\frac{1}{2} \delta^2 f / \delta B^2 = 3 \text{ kHz/G}^2$   
for  $\delta B = 1 \text{ mG}$   
 $\tau_2(\delta\phi = 1 \text{ rad}) \cong 53 \text{ s}$



# Robust memory coherence times





Coherence time  $14.7 \pm 1.6$  s

Ratio of coherence time to error correction time:  $\epsilon \sim 10^{-5}$

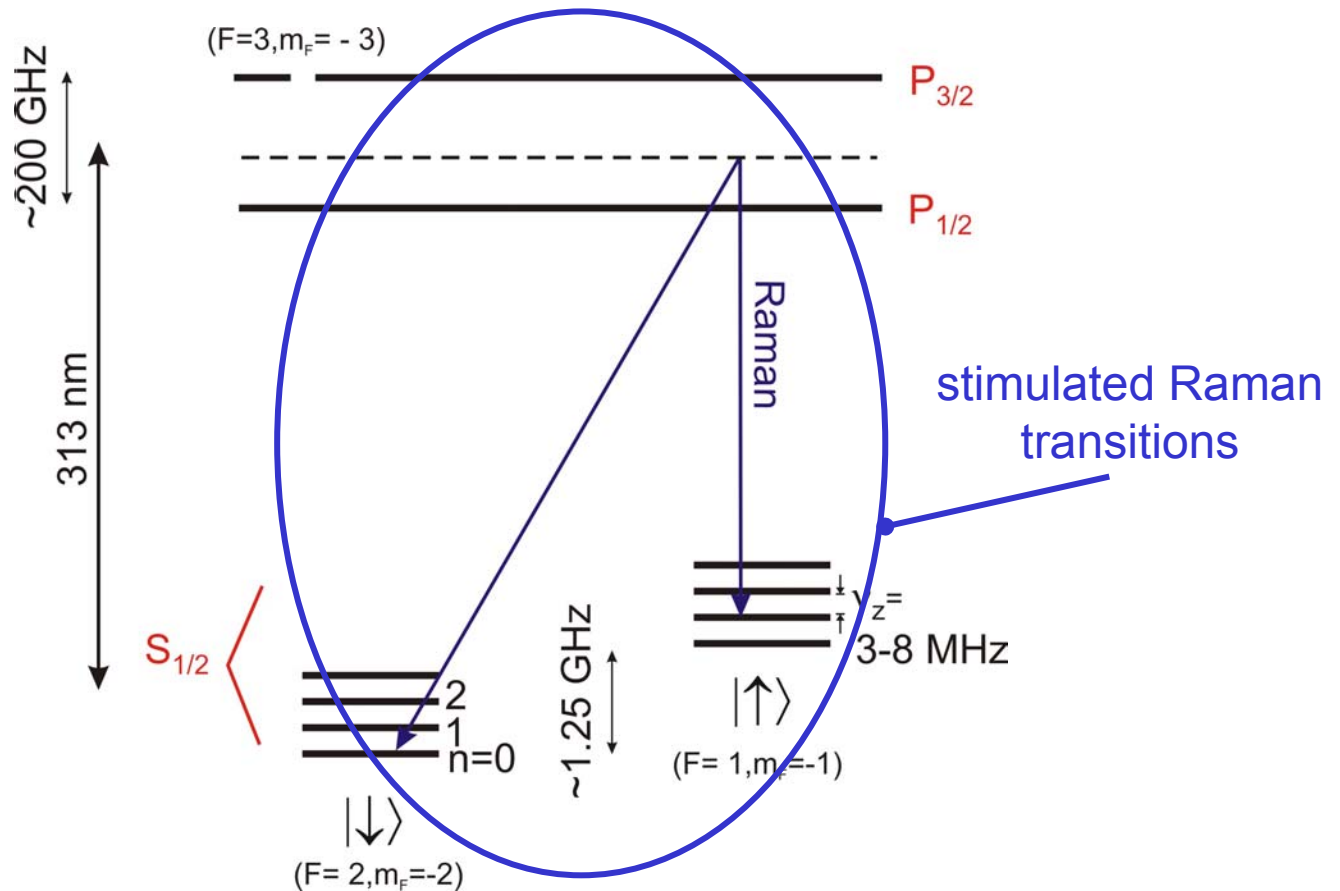
C. Langer *et al.*, PRL **95** 060502 (2005), see also poster M01

# DiVincenzo requirements

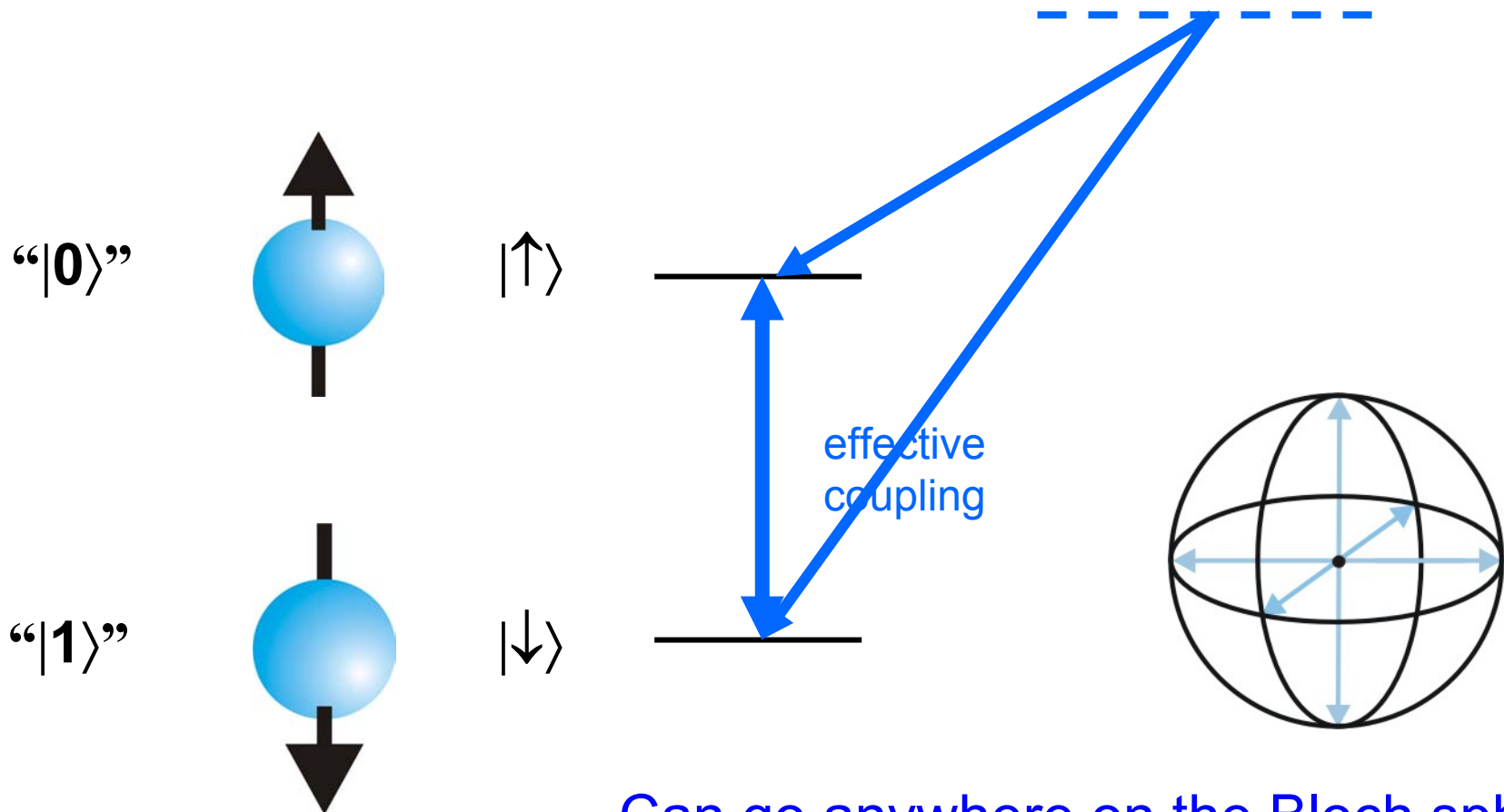
- I. A scalable physical system with well characterized qubits
- II. The ability to initialize the state of the qubits to a simple fiducial state  
optical pumping, ground-state cooling (99.9%) 
- III. Long relevant decoherence times, much longer than the gate time  
Hyperfine ground states  $T_{\text{dec}} > 10$  sec demonstrated 
- IV. A universal set of quantum gates (single qubit rot., two qubit gate)
- V. A qubit-specific read out capability



# Single qubit rotations



# Single qubit rotation: stimulated Raman transitions



Can go anywhere on the Bloch sphere  
Typical  $\pi$ -pulse time:  $1\ \mu\text{s}$   
Fidelity:  $>99\%$

# Boosting fidelity in single qubit rotations

**Main obstacles to single qubit rotation errors  $\approx 10^{-4}$ :**

- 1) Frequency errors, negligible in Raman transitions
- 2) Intensity errors, currently order 5%, need to be reduced to  $<10^{-2}$
- 3) Errors due to spontaneous emission, need to be reduced to  $<10^{-2}$

**Possible improvements for 2):**

- Quieter laser systems, intensity stabilization, active feedback
- Use microwaves to drive single-qubit rotations  
(new issues with cross talk and addressing, especially on large array chips)

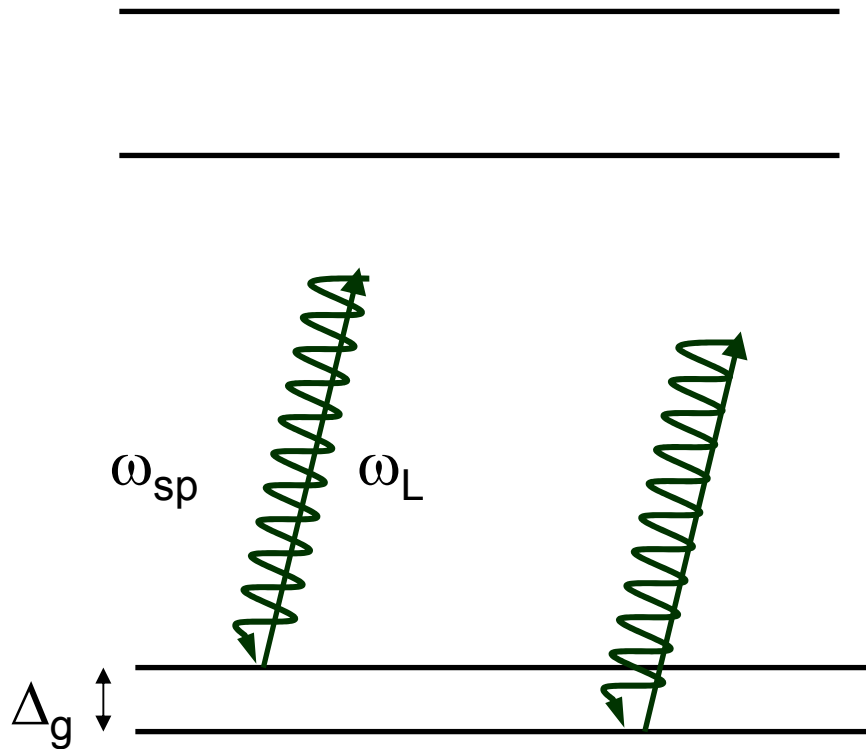
**Possible improvements for 3):**

- Go to larger detunings, requires more powerful laser systems (see poster M20)
- Use microwaves to drive single-qubit rotations

# Spontaneous scattering

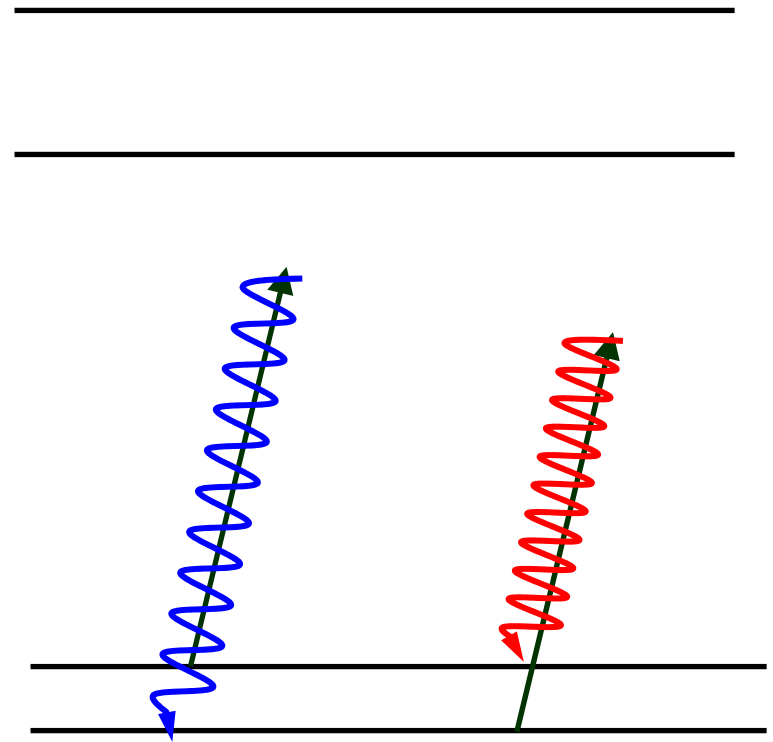
Several hyperfine ground states:

Rayleigh **elastic** scattering



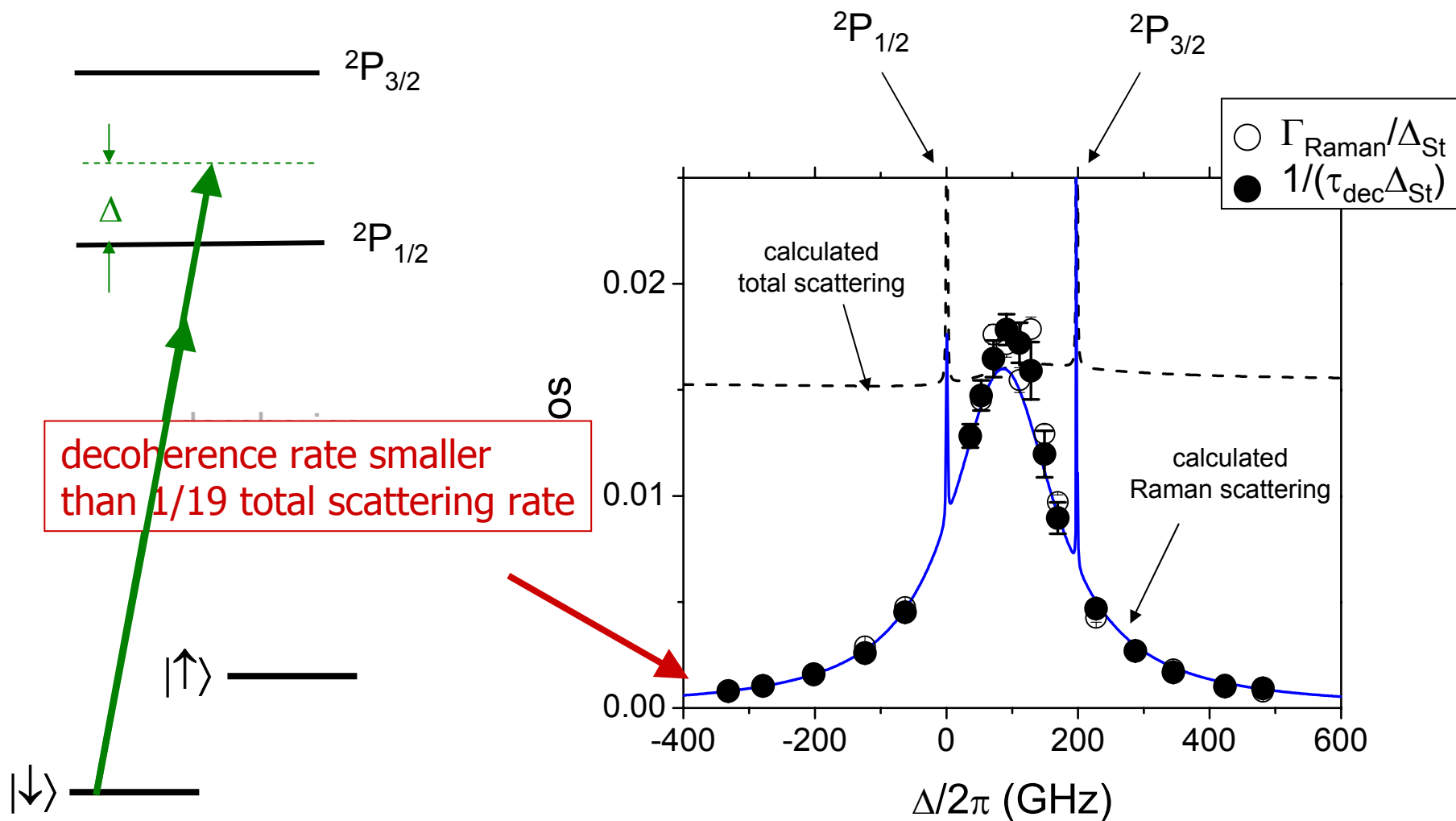
No **information** about the internal state of the atom is carried out by the scattered photon.

Raman **inelastic** scattering



Scattered photon frequency and polarization are **entangled** with the atoms' internal state.

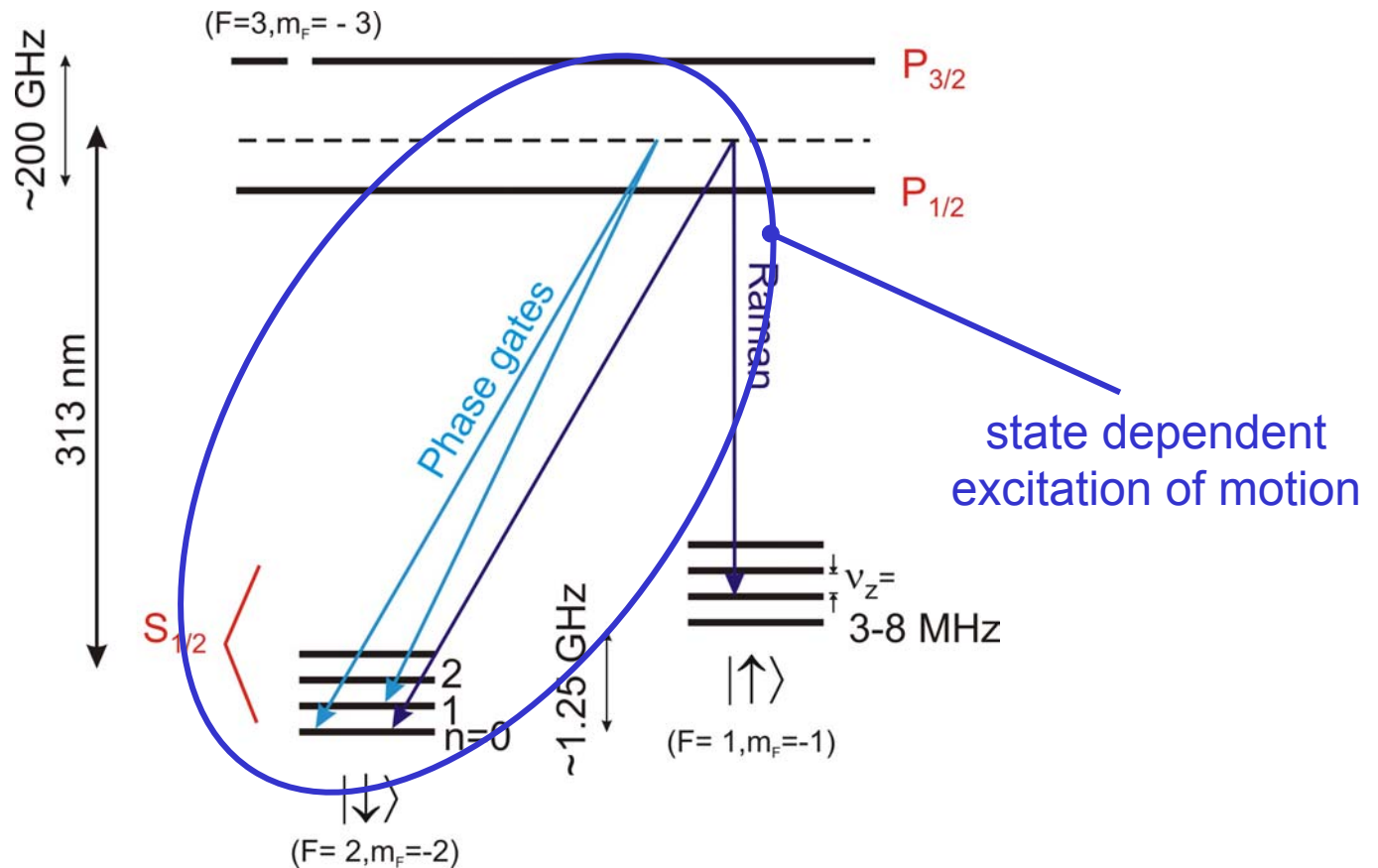
# Decoherence vs. detuning



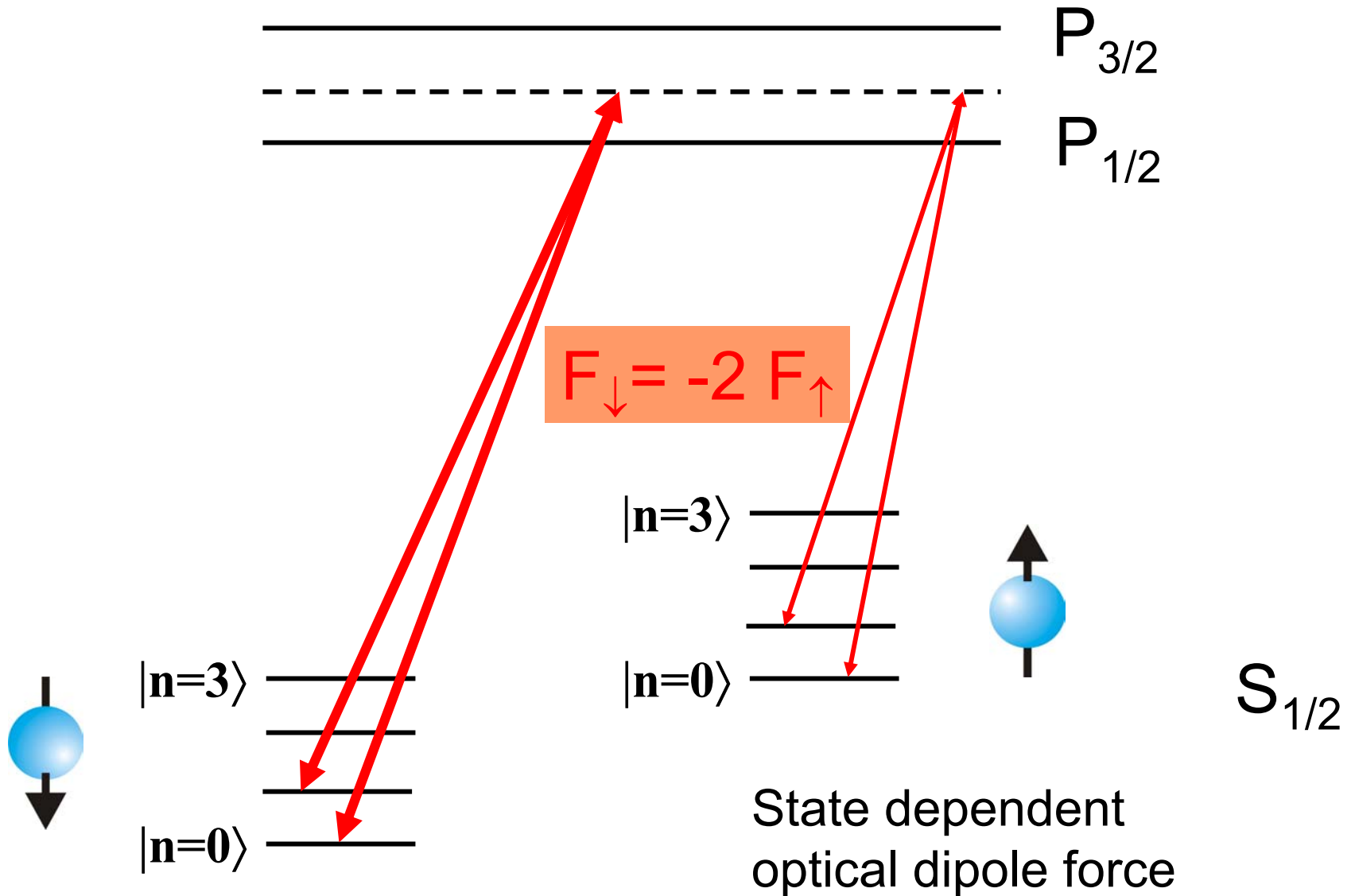
Raman scattering reduces as  $\Delta^2$  when  $\Delta > \Delta_f$  largely independent of FS splitting

R. Ozeri, et. al. Phys. Rev. Lett. **95** 030403 (2005), see also poster M20.

# Two qubit gates

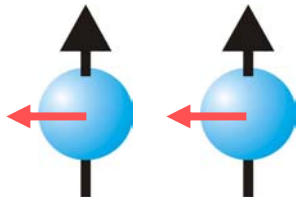


# Motional excitation

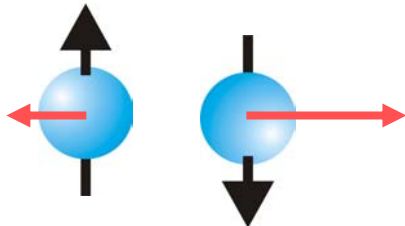
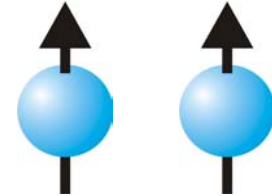




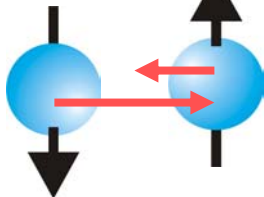
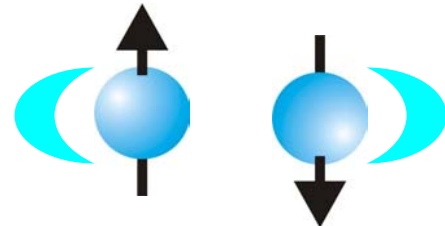
# Stretch mode excitation



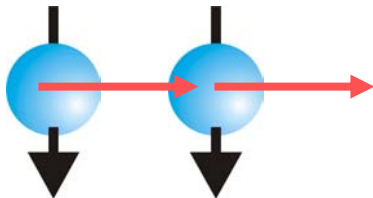
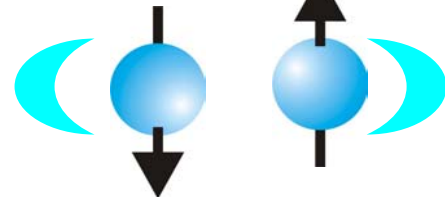
no differential force



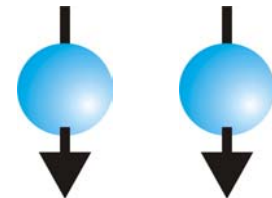
differential force



differential force



no differential force



# Phase gate truth table and properties

$$|\downarrow\downarrow\rangle \rightarrow |\downarrow\downarrow\rangle$$

$$|\downarrow\uparrow\rangle \rightarrow e^{i\phi} |\downarrow\uparrow\rangle$$

$$|\uparrow\downarrow\rangle \rightarrow e^{i\phi} |\uparrow\downarrow\rangle$$

$$|\uparrow\uparrow\rangle \rightarrow |\uparrow\uparrow\rangle$$

Gate fidelity: 97%

Gate time:  $7 \mu\text{s}$  (ca.  $25/v_{\text{COM}}$ )

D. Leibfried *et al.*, Nature **422**, 414 (2003)

Theory: Milburn, Sørensen&Mølmer

# Boosting fidelity in two-qubit gates

**Main obstacles to two-qubit gate errors  $\approx 10^{-4}$ :**

- 1) Motional frequency errors due to trap potential fluctuations
- 2) Intensity errors, currently order 5%, need to be reduced to  $<10^{-2}$
- 3) Errors due to spontaneous emission, order 2%, need to be  $<10^{-4}$
- 4) Z-phase gates only work on field dependent sub-states, MS gates o.k.

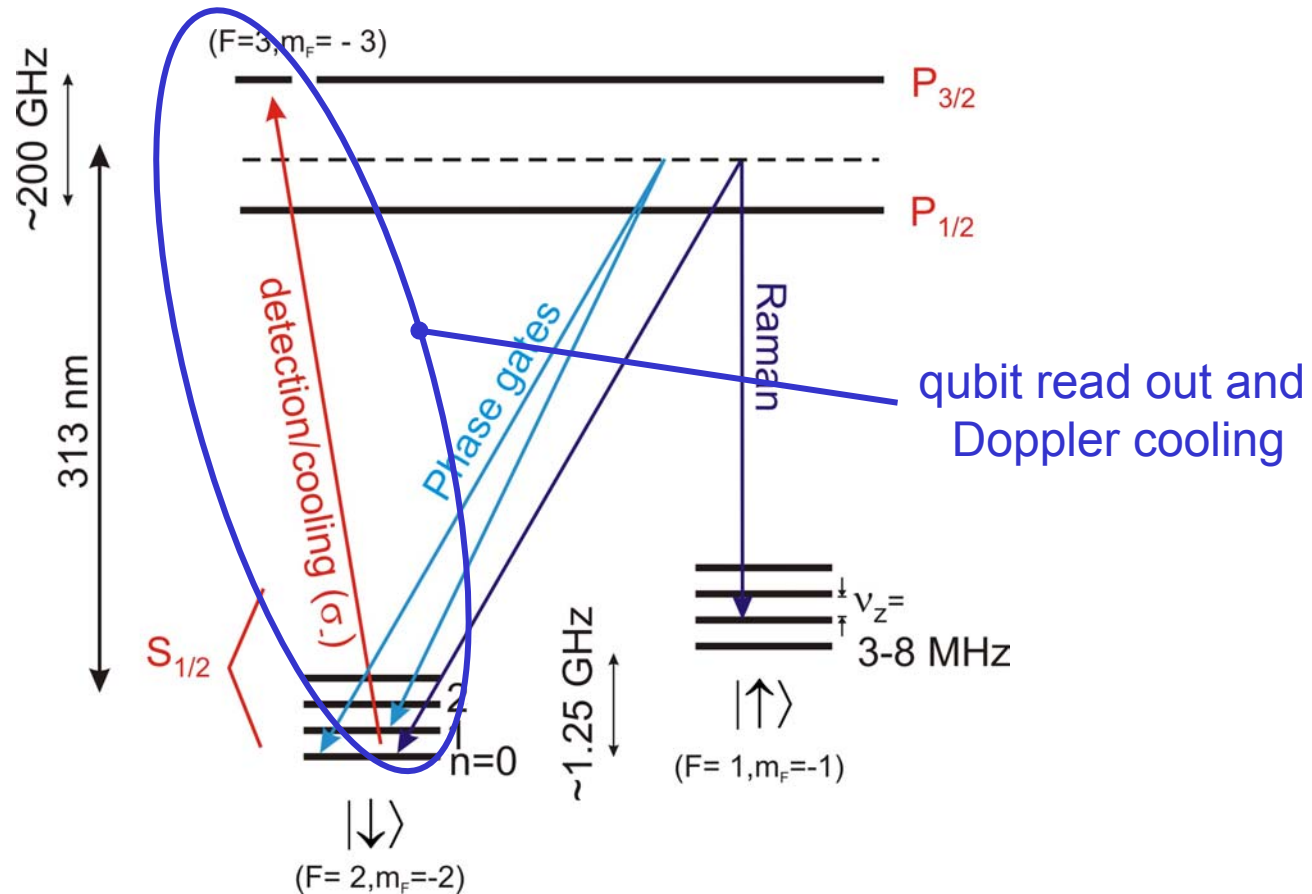
**Possible improvements:**

- 1) Quieter electrode control systems, minimize stray charges and other perturbations
- 2) Quieter laser system, active feedback on laser intensity
- 3) More powerful lasers (can then go to larger detuning, see Poster M20)
- 4) Use Mølmer-Sørensen type gate or momentarily transfer out of field independent state(s).

# DiVincenzo requirements

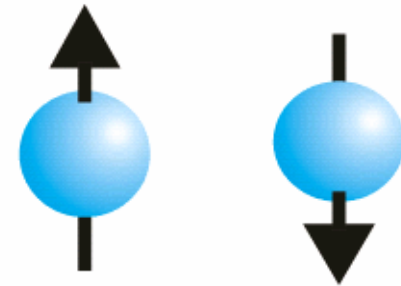
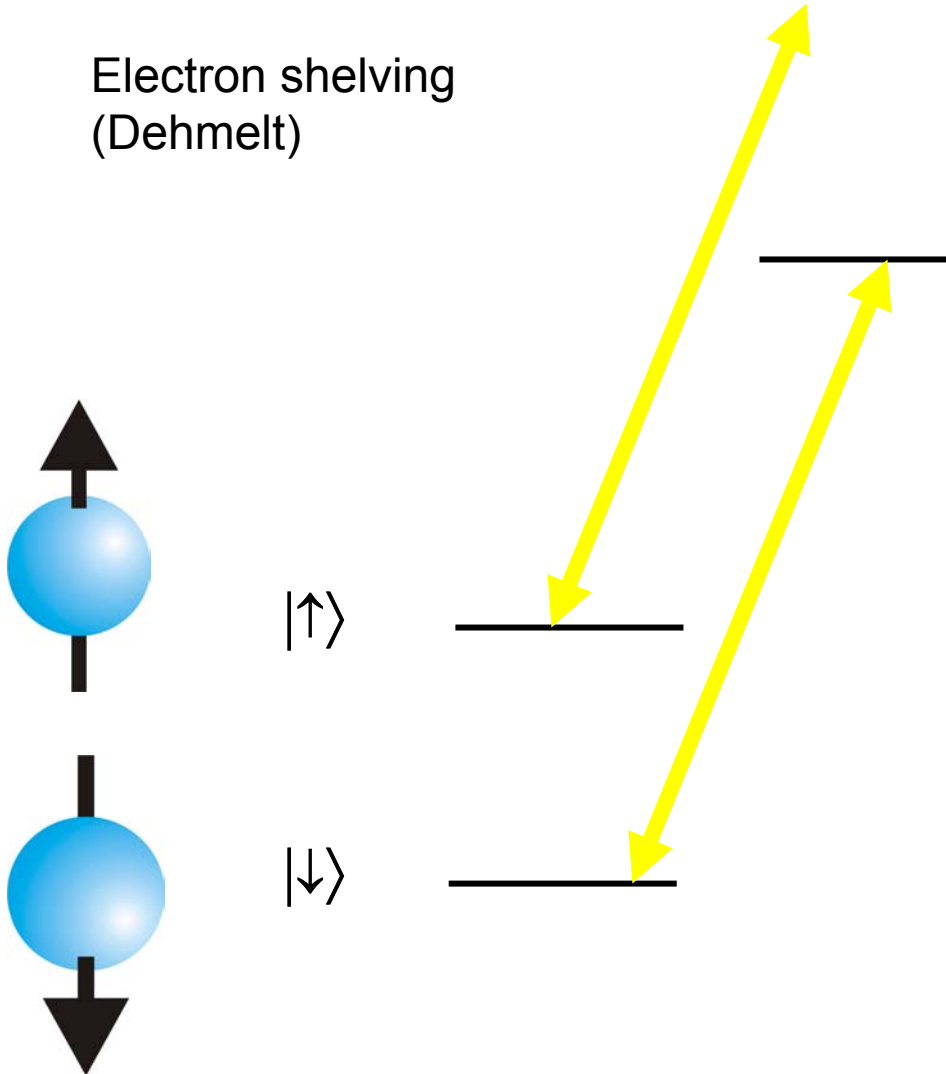
- I. A scalable physical system with well characterized qubits
- II. The ability to initialize the state of the qubits to a simple fiducial state  
optical pumping, ground-state cooling ✓
- III. Long relevant decoherence times, much longer than the gate time  
Hyperfine ground states  $T_{\text{dec}} > 10 \text{ s}$  demonstrated ✓
- IV. A universal set of quantum gates (single qubit rot., two qubit gate)  
co-carrier rotations, phase gate ✓
- V. A qubit-specific read out capability

# Example qubit: $^9\text{Be}^+$



# Qubit readout

Electron shelving  
(Dehmelt)



Be<sup>+</sup> (NIST):  
200  $\mu$ s detection period  
10 counts in  $|\downarrow\rangle$   
0.1 counts in  $|\uparrow\rangle$   
>99% state discrimination

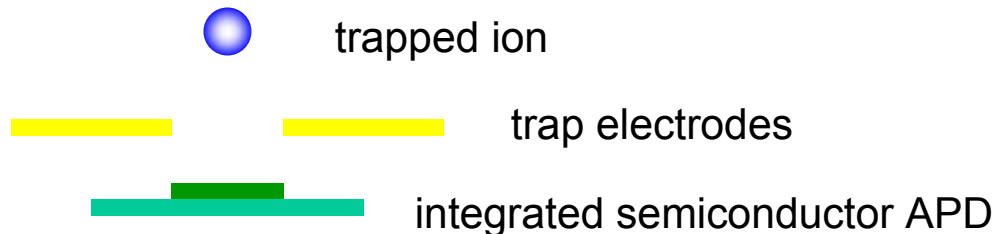
# Scale-up of qubit readout

Currently read-out is based on bulky high NA free-space optics.

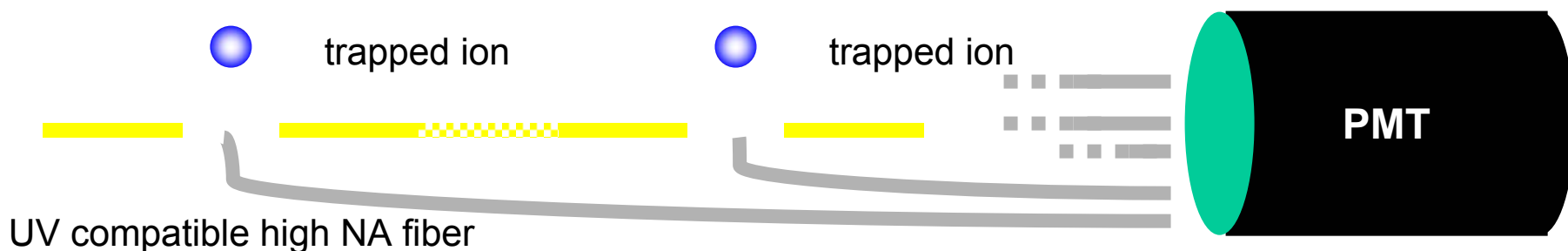
Parallel, fault tolerant architecture requires multi-zone readout.

Will need specialized detection schemes:

- i) On chip optics-free detectors (see also M. Crawford and J.S. Kim)



- ii) On chip fiber-bundle multiplexing to external PMT(s) (only quasi-parallel)



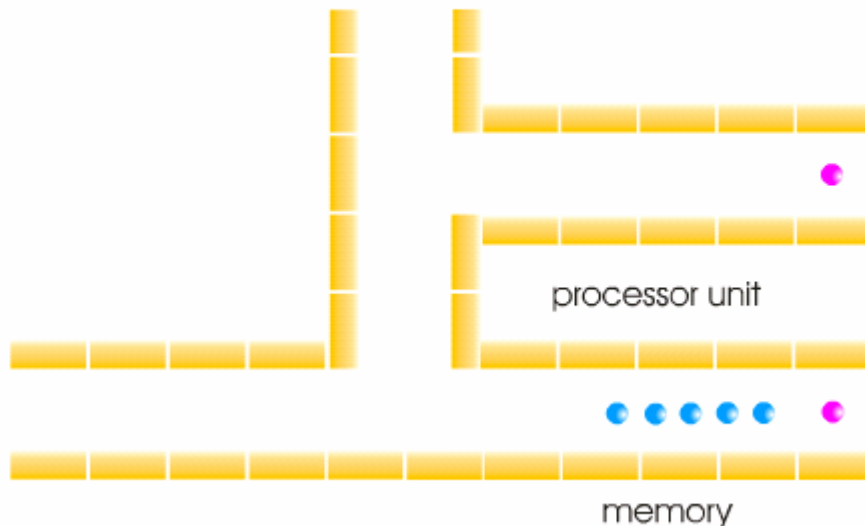


# DiVincenzo requirements

- I. A **scalable** physical system with well characterized qubits
- II. The ability to initialize the state of the qubits to a simple fiducial state  
optical pumping, ground-state cooling (99.9%)  $\Rightarrow |\downarrow\downarrow\downarrow\downarrow\downarrow\dots\rangle |0\rangle$  ✓
- III. Long relevant decoherence times, much longer than the gate time  
 $T_{\text{dec}} > 10 \text{ s}$ ,  $T_{\text{gate}} = 10 \mu\text{s}$ , heating irrelevant ✓
- IV. A universal set of quantum gates (single qubit rot., two qubit gate)  
co-carrier rotations, geometric-phase gate, heating tolerable ✓
- V. A qubit-specific read out capability  
electron shelving method, 99% readout efficiency (100%) ✓

# NIST Multiplexed trap architecture

extension of J. I. Cirac and P. Zoller, PRL **74**, 4091 (1995).



interconnected multi-trap structure  
subtraps completely decoupled

routing of ions by controlling  
electrode voltages

processor sympathetically cooled  
only need to cool three normal modes  
no need for ground state cooling  
in memory

no individual optical addressing  
during two-qubit gates  
can do gates in tight trap

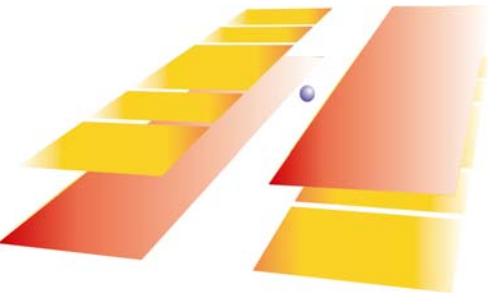
one-qubit gates in extra subtrap  
ion is strongly confined and  
easily addressed

readout in extra subtrap  
no rescattering of fluorescence

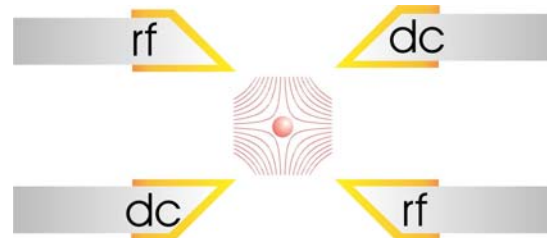
D. J. Wineland, *et al.*,  
J. Res. Nat. Inst. Stand. Technol. **103**, 259 (1998);  
D. Kielpinski, C. Monroe, and D. J. Wineland,  
Nature **417**, 709 (2002).  
Other proposals: DeVoe, Phys. Rev. A **58**, 910 (1998) .  
Cirac & Zoller, Nature **404**, 579 ( 2000), Duan *et al.*

# Two layer Paul trap

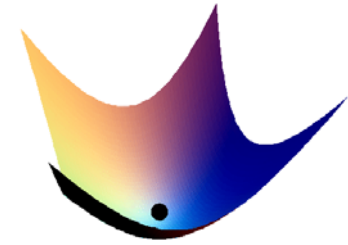
radial confinement:



radial cross section



ac quadrupole field



harmonic time averaged  
pseudo-potential

axial confinement:



axial cross section

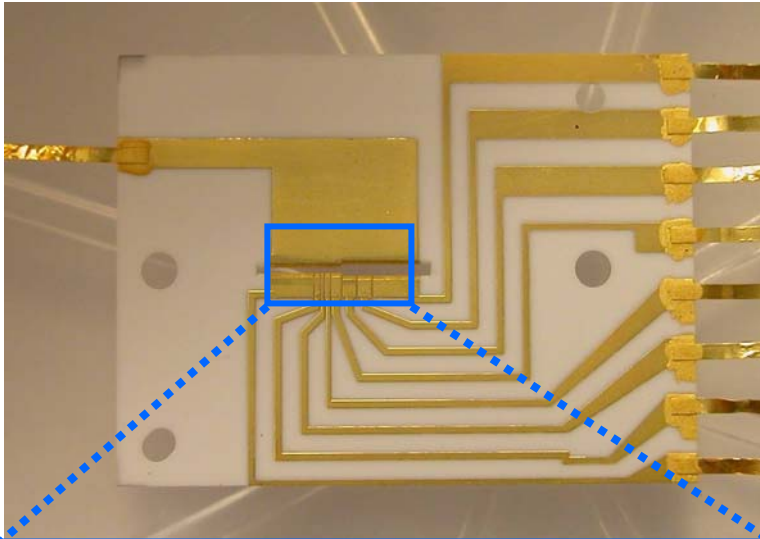


static harmonic axial potential

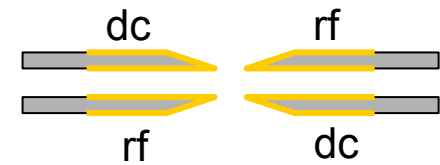


radial conf.  $\gg$  axial conf.  
 $\Rightarrow$  ions align along trap axis

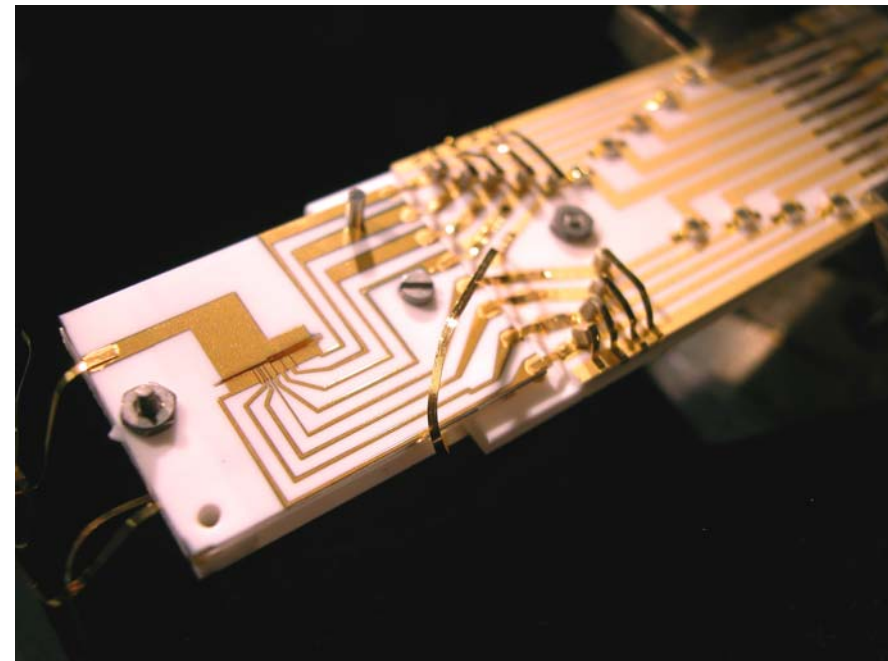
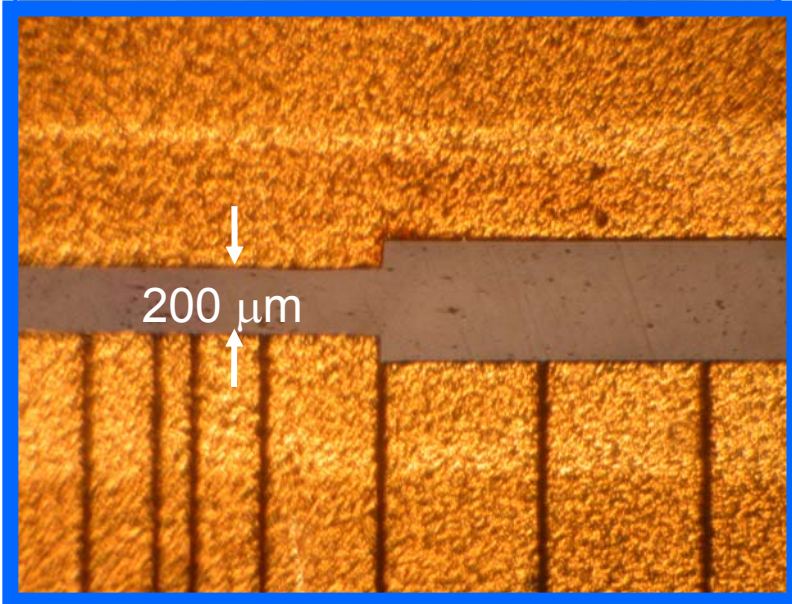
# Two Layer Trap Technology



2 wafers of alumina (0.2 mm thick)  
gold conducting surfaces (2  $\mu\text{m}$ )



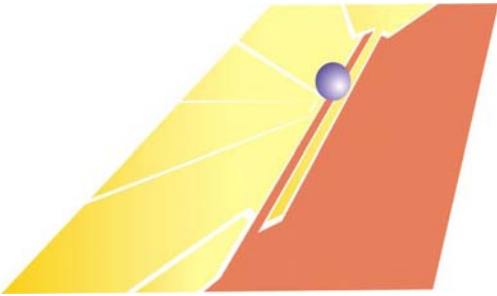
6 zones, dedicated loading zone



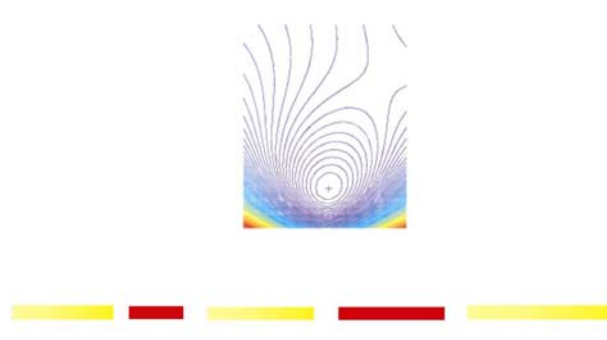
Murray Barrett/John Jost

# Surface trap

radial confinement:

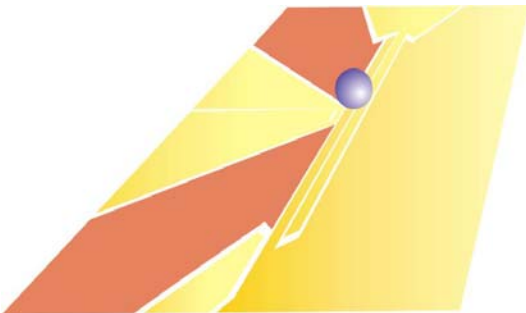


radial cross section



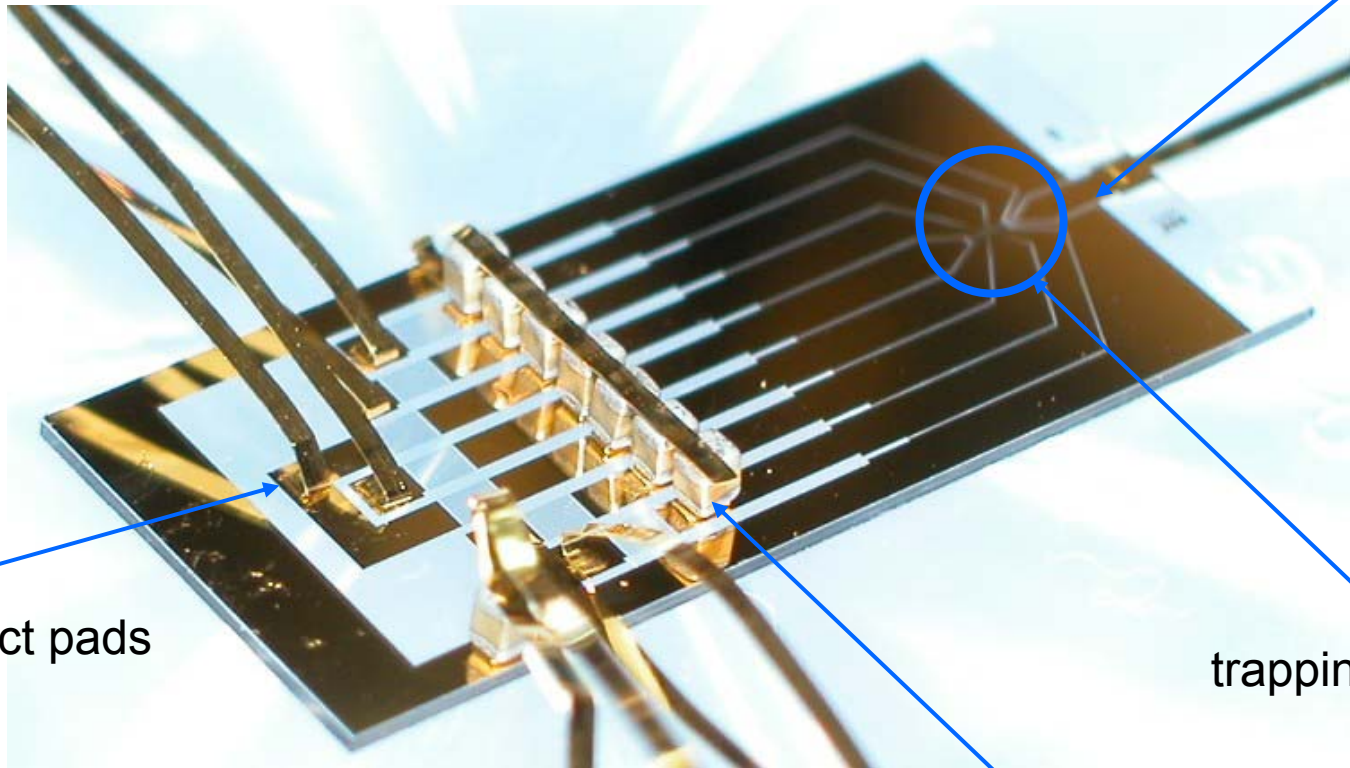
time averaged pseudo-potential

axial cross section



# Planar Trap Chip

Gold on fused silica



RF

DC Contact pads

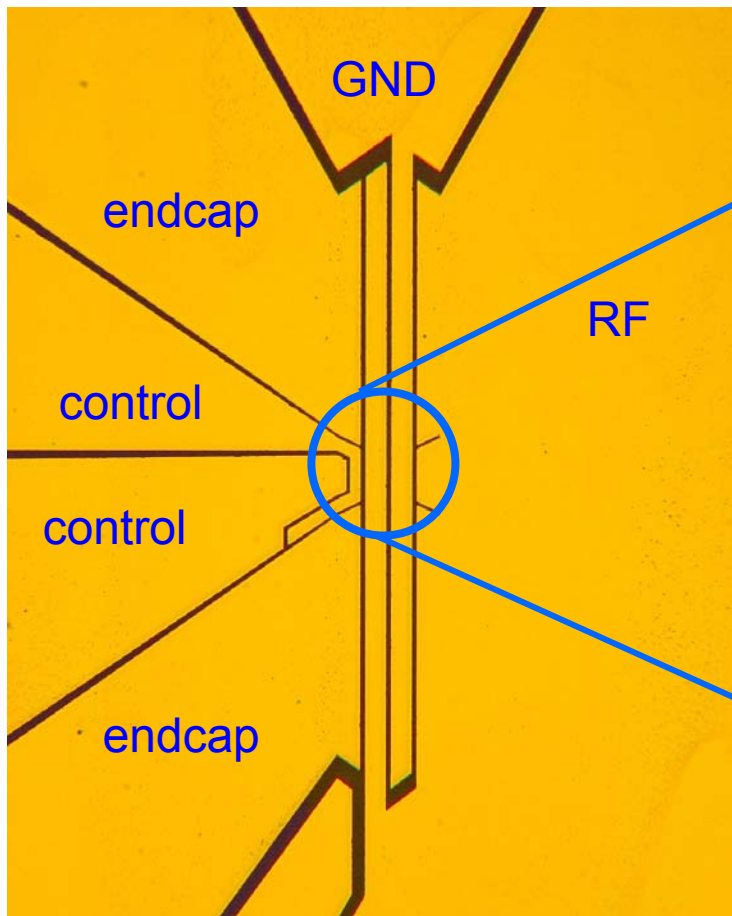
trapping region

low pass filters

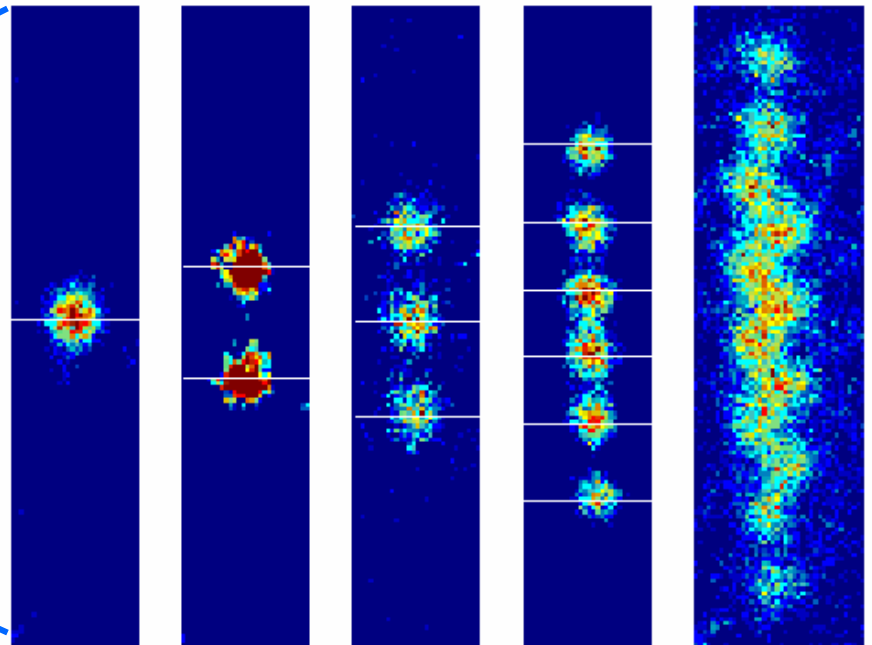


# Planar Trap Chip

Magnified trap electrodes



CCD pictures of strings of  $\text{Mg}^+$  ions  
(trapped 40  $\mu\text{m}$  above surface)

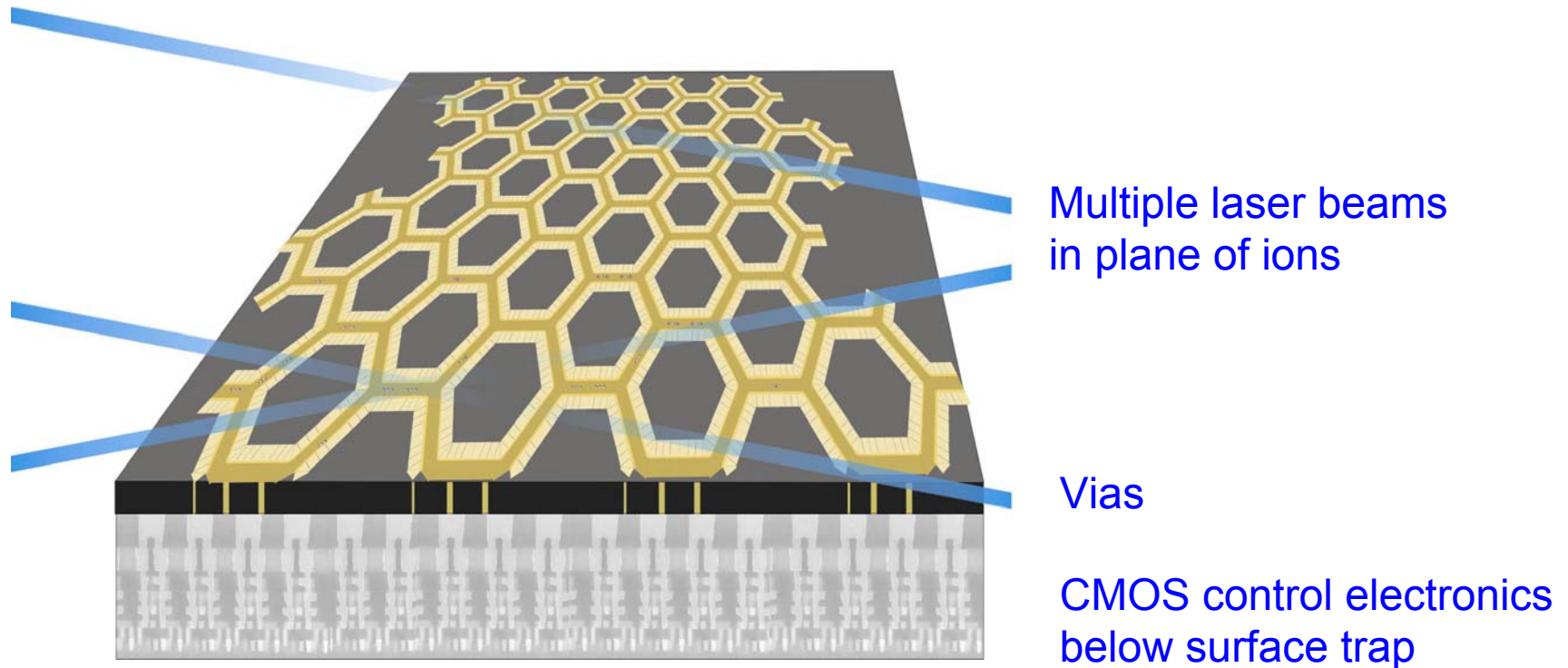


Estimated heating rate  $< 5$  quanta/ms



# The future: Integrated ion chips ?

Large trap array, how to turn corners, **see also poster T01**



“Solid state” with the bulk separated from qubits

ARDA/NSA Fabrication initiative:

Collaborations with Lucent Technology and Sandia Nat. Lab., see other talks

# Multi-Qubit Algorithms

*Towards Heisenberg-Limited Spectroscopy with Multiparticle Entangled States,*  
Science **304**, 1476 (2004).

*Deterministic quantum teleportation of atomic qubits,*  
Nature **429**, 737 (2004).

*Quantum Dense Coding with Atomic Qubits,*  
Phys. Rev. Lett. **93**, 040505 (2004).

*Realization of quantum error correction,*  
Nature **432**, 603 (2004).

*Enhanced Quantum State Detection Efficiency through Quantum Information Processing,*  
Phys. Rev. Lett. **94**, 010501 (2005).

*Implementation of the Semiclassical Quantum Fourier Transform in a Scalable System,*  
Science **308**, 997 (2005).

*Creation of a six-atom ‘Schrödinger cat’ state,*  
Nature **438**, 639 (2005).

In progress: *Entanglement purification*, see also poster M25

# Multi-Qubit Algorithms

*Realization of quantum error correction,*  
Nature **432**, 603 (2004).

More algorithms: [see poster M25](#)

# Why quantum error correction ?

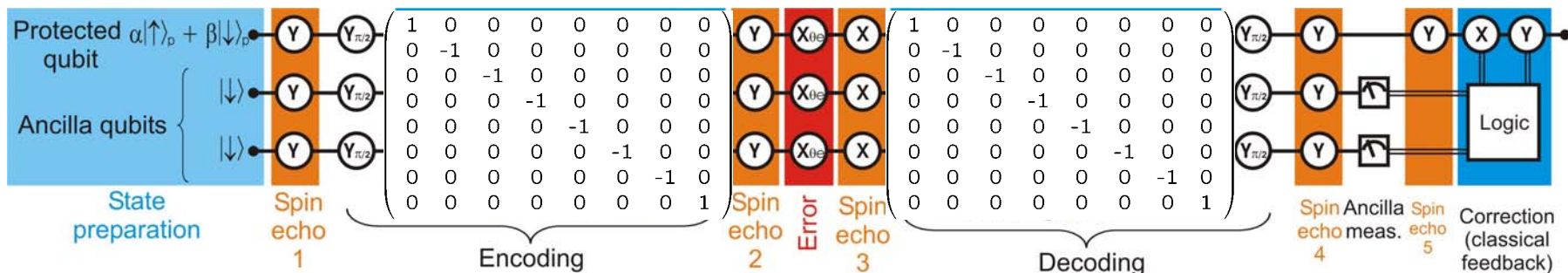
Quantum error correction upgrades large scale quantum computing from  
“Totally hopeless”  
to  
“Theoretically not hopeless”

Will almost certainly be required in large scale computer

Threshold theorem: If individual operation errors are sufficiently small  
we can do arbitrarily long calculations  
(for more disclaimers, see e.g. Ike Chuang’s talk).

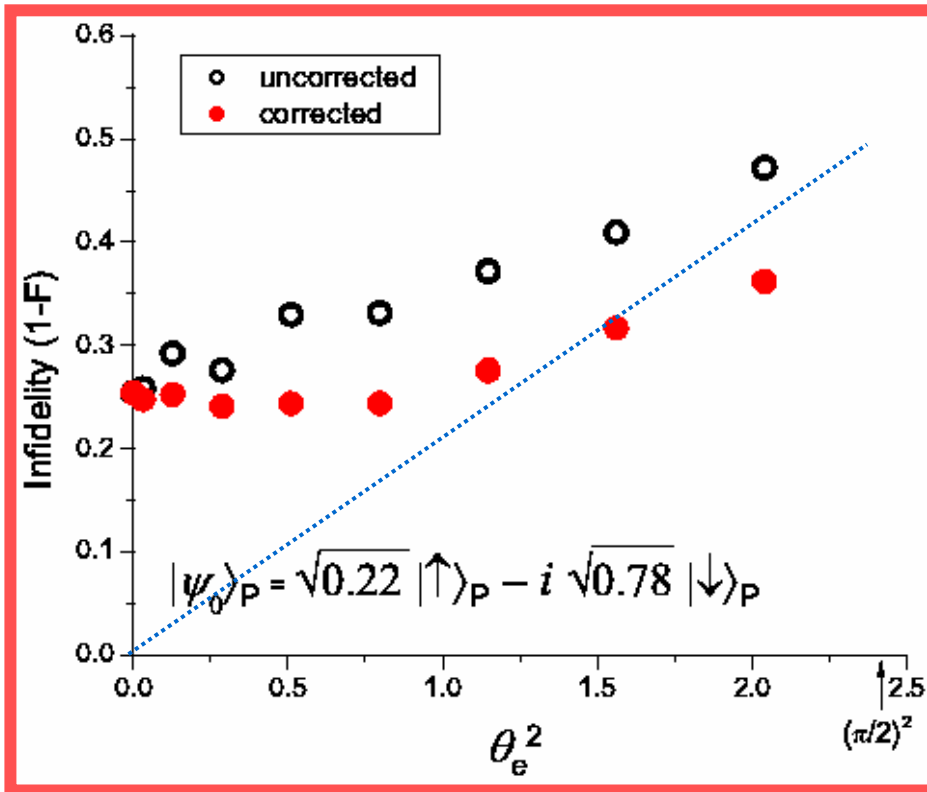
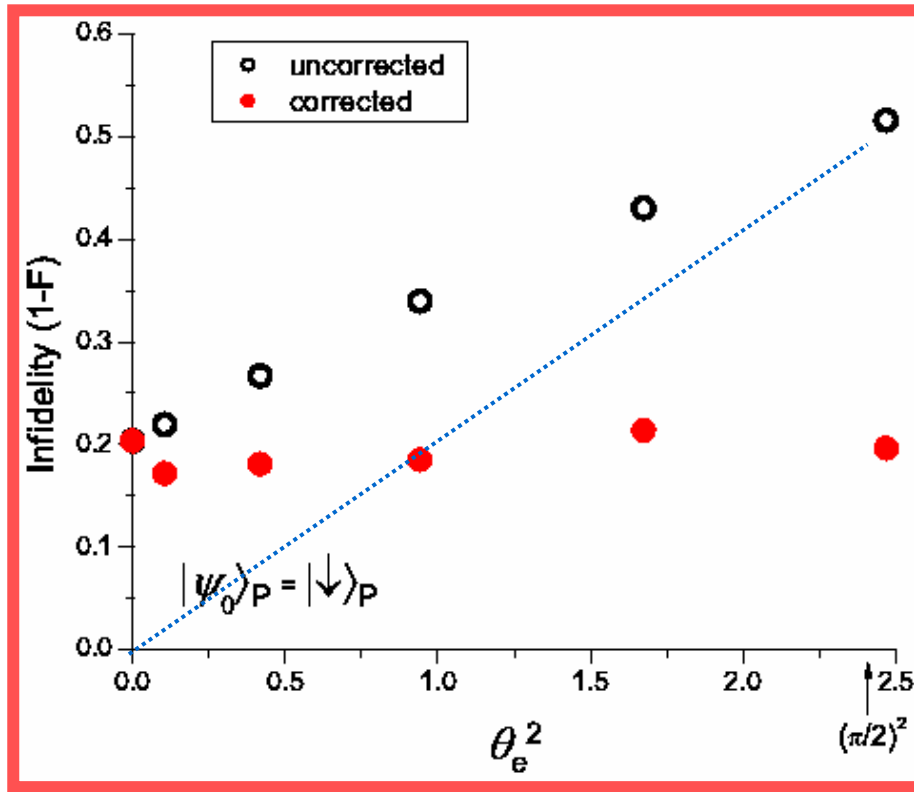
# 3 Qubit Bitflip Error-Correction

- experimental error correction with classical feedback from *measured* ancillas
- based on new stabilizer code with generators  $\{ZZX, ZXZ\}$  (no classical analog)



encoding/decoding gate (G) implemented with single step geometric phase gate

# Error-Correction Results



- Uncorrected infid.  $\sim \theta_e^2$ , corrected infid.  $\sim \theta_e^4$

# Next steps towards scalability

## **Elements that need to be demonstrated in trap array:**

- 1) Shuttle ions in 2D with minimal heating
- 2) DAC electrode control that combines speed with low noise/crosstalk
- 3) On chip/in vacuum multiplexing of electrode control
- 4) Ion reservoir to quickly replace lost qubits

## **Elements that need to be demonstrated in ion control:**

- 1) Repetitive sequences with multi-qubit gates, movement and recooling
- 2) Fast motion/separation approaching the adiabatic limit
- 3) Multiplexing of laser interactions over several trap zones
- 4) Automated calibration of ion positions and Rabi frequencies

## **Elements that need to be demonstrated in ion readout:**

- 1) Simultaneous readout in multiple zones (important for error correction and parallelism)